#### Thyristors **Datasheet**

RoHS

Industry Standard TO-220

■ High Commutating di/dt – 9.0

A/ms minimum at 125°C

These Devices are Pb-Free and are RoHS Compliant

 Operational in Three Quadrants, Q1, Q2, and Q3

Package

Po

## MAC15M, MAC15N TRIAC - 400V - 800V



## **Additional Information**





Resources

Accessories



Samples

## **Description**

Designed for high performance full-wave AC control applications where high noise immunity and high commutating di/dt are required.

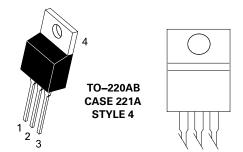
#### **Features**

- Blocking Voltage to 800 Volts
- On-State Current Rating of 15 Amperes RMS at 80°C
- Uniform Gate Trigger Currents in Three Modes
- High Immunity to dv/dt 250 V/µs minimum at 125°C
- Minimizes Snubber Networks for Protection

### **Functional Diagram**









## Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1)MAC15M(Gate Open, Sine Wave 50 to 60 Hz, $T_j = -40^{\circ}$ to 125°C)MAC15N		V <sub>drm</sub> , V <sub>rrm</sub>	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 8$	80°C)	I <sub>T (RMS)</sub>	15	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>c</sub> = 125°C)	I <sub>TSM</sub>	150	А	
Circuit Fusing Consideration (t = 8.3 ms)	l²t	93	A <sup>2</sup> sec	
Peak Gate Power ( $T_c = 80^{\circ}$ C, Pulse Width <= 1.0 µs)	P <sub>GM</sub>	20	W	
Average Gate Power (t = 8.3 ms, $T_c = 80^{\circ}$ C)	P <sub>G(AV)</sub>	0.5	W	
Operating Junction Temperature Range	T,	-40 to +125	°C	
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the

Recommended Operating Conditions may affect device reliability.
1. V<sub>DBM</sub> and V<sub>RBM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

## **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		TL	260	°C

### Electrical Characteristics - OFF (TJ = 25°C unless otherwise noted ; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Мах	Unit
eak Repetitive Blocking Current T <sub>1</sub> = 25°C		I <sub>DRM</sub> ,	-	-	0.01	mA
$(V_{D} = V_{DRM} = V_{RRM}; \text{ Gate Open})$	T _ = 125°C	I	-	-	2.0	IIIA

#### Electrical Characteristics - ON (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Мах	Unit
Peak On–State Voltage (Note 2) ( $I_{TM} = \pm 21$ A Peak)		V <sub>TM</sub>	-	1.2	1.6	V
Gate Trigger Current	MT2(+), G(+)		5.0	13	35	
(Continuous dc)	MT2(+), G(-)	I <sub>gt</sub>	5.0	16	35	mA
$(V_{_{D}} = 12 \text{ V}, \text{ R}_{_{L}} = 100 \Omega)$	MT2(-), G(-)		5.0	18	35	
Gate Trigger Voltage (Continuous dc) ( $V_p = 12 V$ , $R_L = 100 \Omega$ )	MT2(+), G(+)		0.5	0.75	1.5	
	MT2(+), G(-)	V <sub>gt</sub>	0.5	0.72	1.5	V
	MT2(-), G(-)		0.5	0.82	1.5	
	MT2(+), G(+)		-	33	50	
Latching Current ( $V_p = 24 V$ , $I_c = 35 mA$ )	MT2(+), G(-)	V <sub>gd</sub>	_	36	80	V
$(v_D - 2 + v), v_G - 00 m m$	MT2(-), G(-)		_	33	50	
Holding Current ( $V_{D} = 12 V_{dc}$ , Gate Open, Initiating Current = ±150 mA))		I <sub>H</sub>	-	20	40	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%

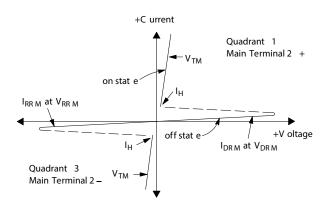


## **Dynamic Characteristics**

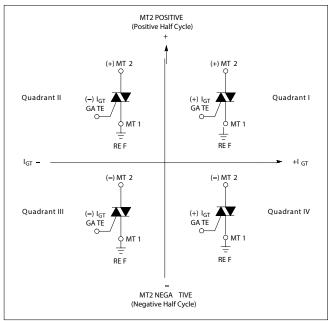
Characteristic	Symbol	Min	Тур	Мах	Unit
Rate of Change of Commutating Current; See Figure 10. ( $V_D = 400 \text{ V}$ , $I_{TM} = 6.0 \text{ A}$ , Commutating dv/dt = 24 V/µs, $C_L = 10 \text{ µF}$ Gate Open, TJ = 125°C, f = 250 Hz, No Snubber) $L_I = 40 \text{ mH}$	(di/dt) <sub>c</sub>	9.0	-	-	A/ms
Critical Rate of Rise of Off-State Voltage ( $V_D = Rated V_{DRM}$ , Exponential Waveform, Gate Open, TJ = 125°C)	dV/dt	250	-	_	V/µs

## **Voltage Current Characteristic of SCR**

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current



## **Quadrant Definitions for a Triac**

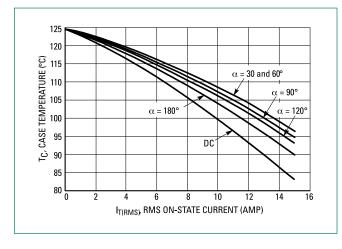


All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used

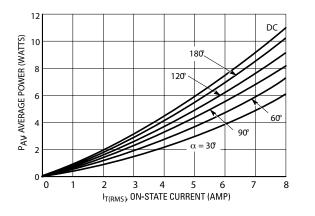


# MAC15M, MAC15N TRIAC - 400V - 800V

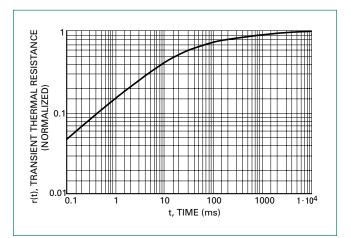


### Figure 1. RMS Current Derating

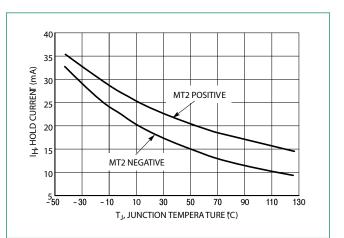




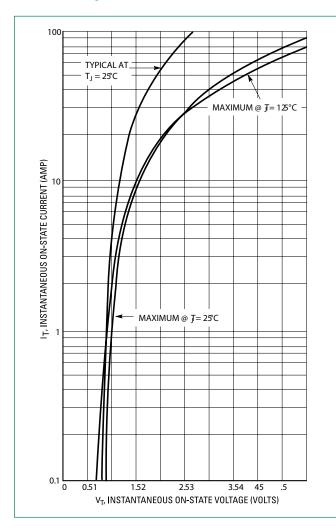
#### Figure 4. Thermal Response



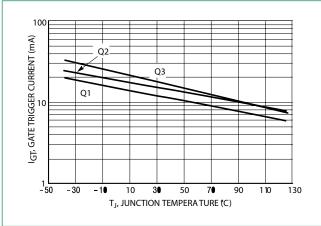
#### Figure 5. Hold Current Variation



#### Figure 3. On–State Characteristics



## MAC15M, MAC15N TRIAC – 400V - 800V



# Figure 6. Gate Trigger Current Variation



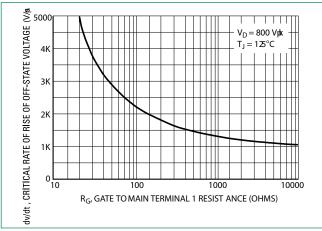
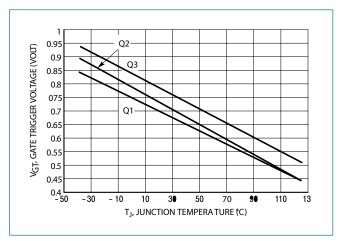
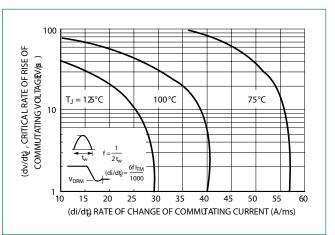


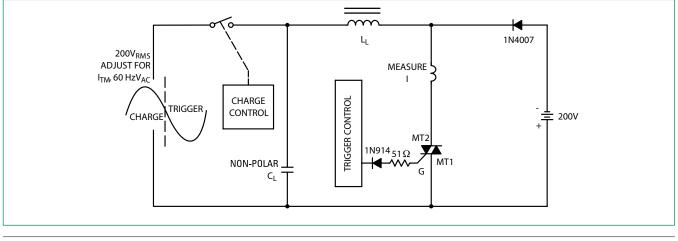
Figure 7. Gate Trigger Voltage Variation





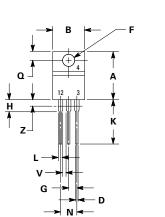


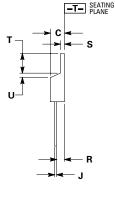




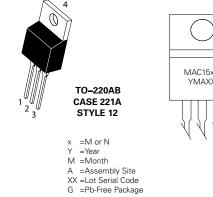
# MAC15M, MAC15N TRIAC - 400V - 800V

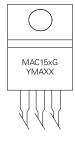
## **Dimensions**





### **Part Marking System**





Dim	Inches		Millimeters			
Dim	Min	Мах	Min	Мах		
Α	0.590	0.620	14.99	15.75		
В	0.380	0.420	9.65	10.67		
С	0.178	0.188	4.52	4.78		
D	0.025	0.035	0.64	0.89		
F	0.142	0.147	3.61	3.73		
G	0.095	0.105	2.41	2.67		
Н	0.110	0.130	2.79	3.30		
J	0.018	0.024	0.46	0.61		
К	0.540	0.575	13.72	14.61		
L	0.060	0.075	1.52	1.91		
Ν	0.195	0.205	4.95	5.21		
٥	0.105	0.115	2.67	2.92		
R	0.085	0.095	2.16	2.41		
S	0.045	0.060	1.14	1.52		
т	0.235	0.255	5.97	6.47		
U	0.000	0.050	0.00	1.27		
v	0.045		1.15			
Z		0.080		2.04		

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	Main Terminal 2			

## **Ordering Information**

Device	Package	Shipping
MAC15MG	TO-220AB	1000 Unite / Day
MAC15NG	(Pb-Free)	1000 Units / Box

1. Dimensioning And Tolerancing Per Ansi Y14.5m, 1982.

Controlling Dimension: Inch.
 Dimension Z Defines A Zone Where All Body And Lead Irregularities Are Allowed.

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